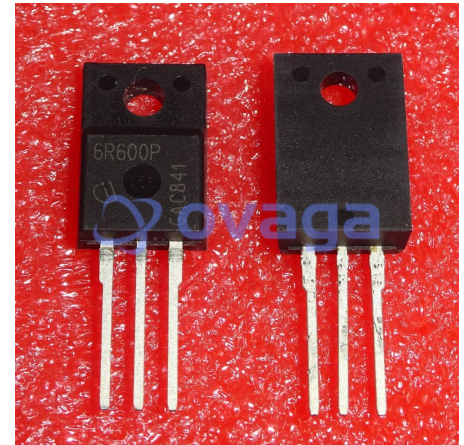


N-Channel MOSFETs (>500V...900V); Package: PG-TO220-3; VDS (max): 600.0 V; Package: TO-220 FullPAK; RDS(ON) @ TJ=25°C VGS=10: 600.0 mOhm; ID(max) @ TC=25°C: 6.1 A; IDpuls (max): 15.0 A; MOSFET COOL MOS PWR TRANS MAX 650V

Manufacturers	Infineon Technologies Corporation
Package/Case	TO-220F
Product Type	Transistors
RoHS	Rohs
Lifecycle	



Images are for reference only

Please submit RFQ for IPA60R600CP or [Email to us: sales@ovaga.com](mailto:sales@ovaga.com) We will contact you in 12 hours.

[RFQ](#)

General Description

IPA60R600CP is a specific model number for a power MOSFET semiconductor device manufactured by Infineon Technologies.

Features

Maximum Drain-Source Voltage (Vds): 600V

Continuous Drain Current (Id): 52A

Maximum Power Dissipation: 280W

Low on-resistance (Rds(on)): 0.12 Ohm

Application

IRFP460APBF

STP55NF06L

FDPF51N25T

2SK3568-01MR

HUF75345G3

SPW20N60S5



Related Products



[IPP60R070CFD7](#)

Infineon Technologies Corporation
TO-220-3



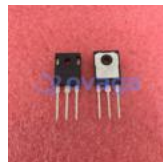
[IPB180N06S4-H1](#)

Infineon Technologies Corporation
PG-TO263-7-3



[IPG20N04S4-12](#)

Infineon Technologies Corporation
TDSON-8



[IPW65R080CFD](#)

Infineon Technologies Corporation
TO-247



[IPD25N06S4L-30](#)

Infineon Technologies Corporation
PG-TO252-3



[IPD180N10N3G](#)

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TO-252



[IPP60R074C6](#)

Infineon Technologies Corporation
TO-220-3



[IPD70R1K4P7S](#)

Infineon Technologies Corporation
TO252-3